

ABSTRACT

A semiconductor device according to this invention includes: two level shift switches (28A and 28B) each having first and second electrodes, a control electrode, a signal output electrode, and a first semiconductor region forming a transistor device section (28a,28b) which intervenes between the first electrode and the signal output electrode and is brought into or out of conduction according to a signal inputted to the control electrode and a resistor device section (Ra,Rb) which intervenes between the signal output electrode and the second electrode, the first semiconductor region comprising a wide bandgap semiconductor; and a diode (23) having a cathode-side electrode, an anode-side electrode, and a second semiconductor region comprising a wide bandgap semiconductor.